

Technical Data Sheet

1.5mm Side Looking Infrared Emitting Diode

SIR908-7P-R

■ Features

- Low forward voltage
- Peak wavelength $\lambda_p=875\text{nm}$
- High reliability



■ Descriptions

The **SIR908-7P-R** is a GaAlAs infrared emitting diode. The miniature side-facing device has a chip that emits radiation from the side of the pink package.

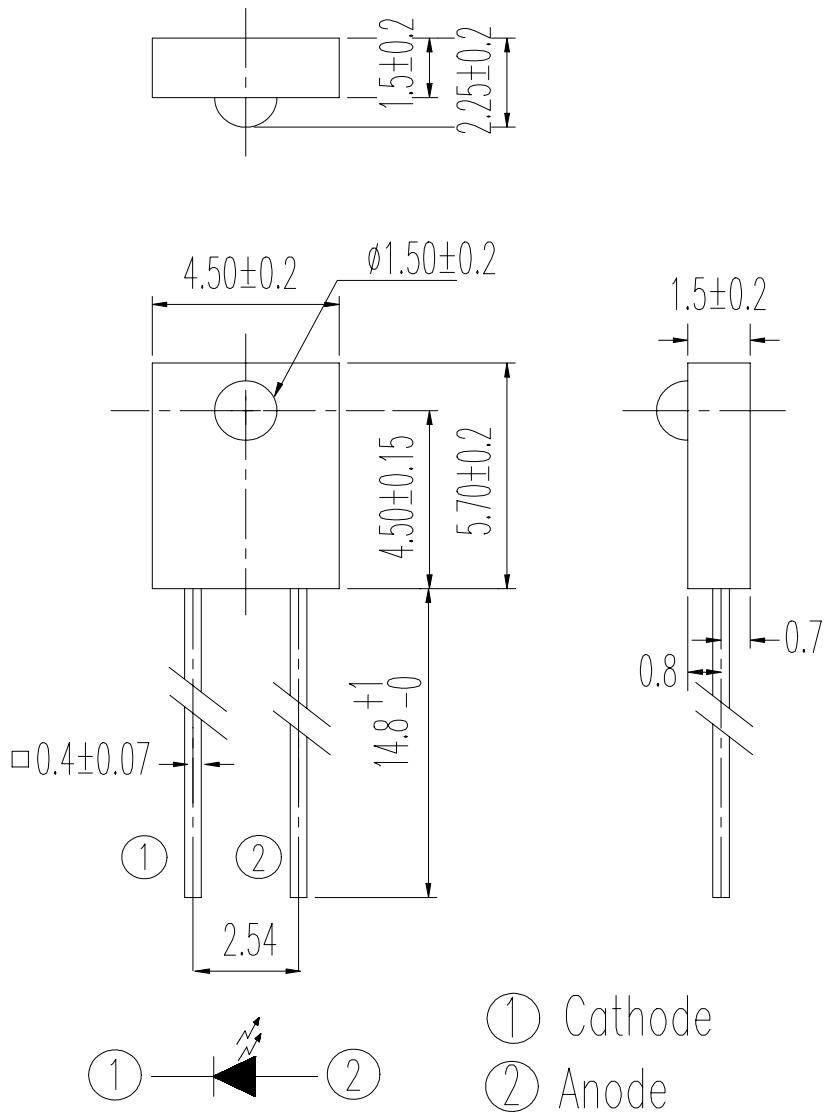
■ Applications

- Optoelectronic switch
- Photo interrupter

■ Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
SIR	GaAlAs	PINK

Device No:**DIS-090-078**

■ Package Dimensions

Notes:

1. All dimensions are in millimeters
2. Tolerances unless dimensions $\pm 0.1\text{mm}$

Device No:DIS-090-078

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I _F	60	mA
Peak Forward Current(*)	I _{FP}	1.0	A
Reverse Voltage	V _R	5	V
Operating Temperature	T _{opr}	-25 ~ +85	°C
Storage Temperature	T _{stg}	-40 ~ +85	°C
Soldering Temperature	T _{sol}	260	°C
Power Dissipation at(or below) 25°C Free Air Temperature	P _d	150	mW

Notes: *1: tw=100 μ SEC., Duty cycle=1%

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Collector current	I _{C(ON)}	V _{CE} =3.5V, I _F =4mA	300	--	1300	μ A
Peak Wavelength	λ _p	I _F =20mA	--	875	--	nm
Spectral Bandwidth	Δ λ	I _F =20mA	--	50	--	nm
Forward Voltage	V _F	I _F =20mA	--	1.3	1.6	V
		I _F =100mA, t _p =100 μ s, t _p /T=0.01	--	1.4	1.8	
		I _F =1A, t _p =100 μ s, t _p /T=0.01	--	2.6	4.0	
Reverse Current	I _R	V _R =5V	--	--	10	μ A
View Angle	2 θ 1/2	I _F =20mA	--	50	--	deg

■ Typical Electro-Optical Characteristics Curves

Fig. 1 Forward Current vs.
Ambient Temperature

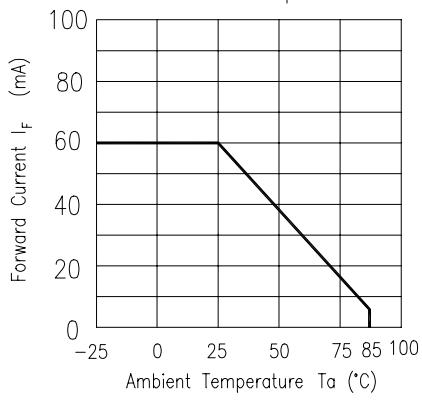


Fig. 3 Peak Emission Wavelength vs.
Ambient Temperature

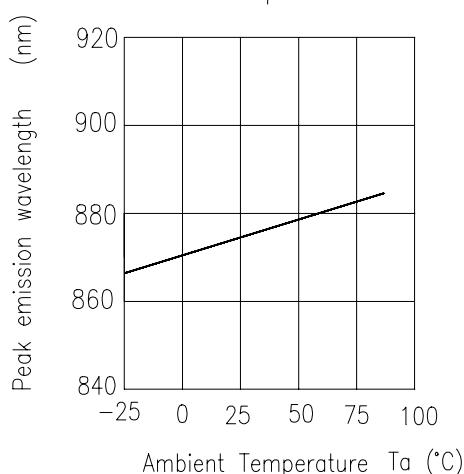


Fig. 5 Forward Current vs.
Ambient Temperature

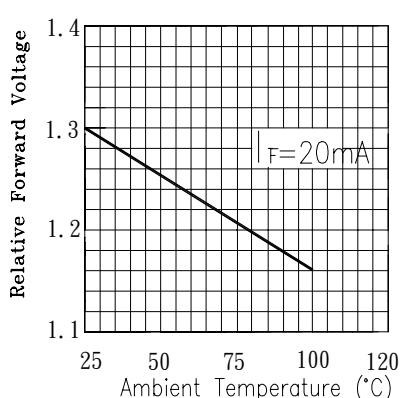


Fig. 2 Spectral Distribution

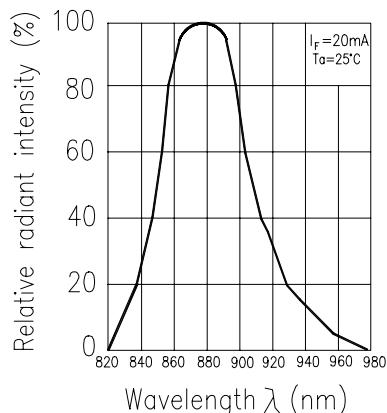


Fig. 4 Forward Current vs.
Forward Voltage

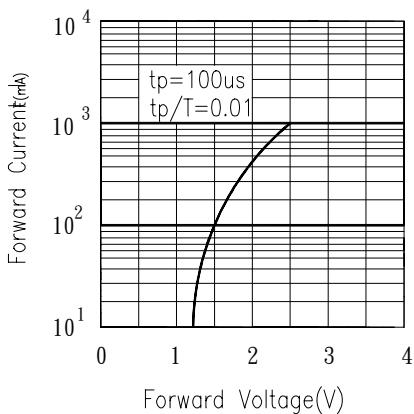
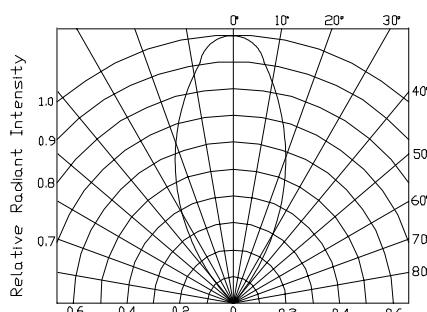


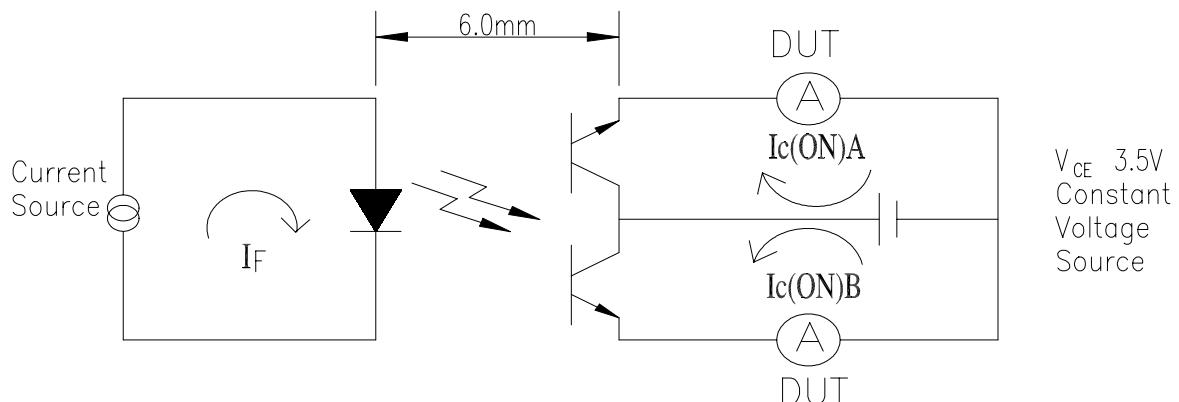
Fig. 6 Relative Radiant Intensity vs.
Angular Displacement



Device No:DIS-090-078

■ Test Method For $I_{C(ON)}$:Condition: $I_F=4\text{mA}$

The intensity testing method for infrared emitting diode

**■ To Distinguish Intensity:**Condition: $V_{CE}=3.5\text{V}$, $I_F=4\text{mA}$ UNIT: μA

Bin Number	7-2	7-1	6-2	6-1
Min	300	340	450	630
Max	450	560	770	1300

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■ Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgment Criteria	Ac/Re
1	Solder Heat	TEMP. : $260^{\circ}\text{C} \pm 5^{\circ}\text{C}$	5secs	22pcs	$I_R \geq U_x \times 2$	0/1
2	Temperature Cycle	H : $+85^{\circ}\text{C}$ L : -55°C	30mins 5mins 30mins	50 Cycles	22pcs $I_{CON} \leq L_x \times 0.8$ $V_F \geq U_x \times 1.3$	0/1
3	Thermal Shock	H : $+100^{\circ}\text{C}$ L : -10°C	5mins 10secs 5mins	50 Cycles	22pcs U : Upper Specification Limit	0/1
4	High Temperature Storage	TEMP. : $+100^{\circ}\text{C}$	1000 hrs	22pcs	L : Lower Specification Limit	0/1
5	Low Temperature Storage	TEMP. : -55°C	1000 hrs	22pcs		0/1
6	DC Operating Life	$I_F = 20\text{mA}$	1000 hrs	22pcs		0/1
7	High Temperature/ High Humidity	$85^{\circ}\text{C} / 85\% \text{ R.H}$	1000 hrs	22pcs		0/1

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